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# **AMENDMENT TRANSMITTAL LETTER**

Docket No. KWM-0001

Application No. 10/088,163

Filing Date March 15, 2002 Examiner P. Greene

Art Unit 2826

Applicant(s): Kazutaka SHIBATA

Invention:

SEMICONDUCTOR DEVICE WITH CHIP-ON-CHIP CONSTRUCTION JOINED VIA A LOW-

MELTING POINT METAL LAYER (AS AMENDED)

#### TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

		CLAIM	S AS AMENI	DED	
	Claims Remaining After Amendment	Highest Number Previously Pald	Number Extra Claims Present	Rate	
Total Claims	33	- 35 =		х	0.00
Independent Claims	4	- 6 =		х	0.00
Multiple Depend	lent Claims (ch	eck if applicabl	e)		
Other fee (pleas	e specify):				
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0.00
x Large Entity Small Entity					ty
x No additiona	al fee is require	d for this ame	ndment.		
	ge Deposit Acc			n the amount of \$	•
A check in the	ne amount of \$		to cover	the filing fee is er	nclosed.
Payment by	credit card. Fo	orm PTO-2038	is attached.		
	ssioner is herel d below. A dup			credit Deposit Adenclosed.	ccount No18-0013
x Credit a	ny overpaymer	nt.			
x Charge a	any additional fili	ing or application	n processing t	ees required unde	r 37 CFR 1.16 and 1.17
Carl Schaukow Attorney Reg. N				Dated:	March 13, 2003
RADER, FISHN 1233 20th Stree Suite 501 Washington, DO (202) 955-3750 Customer No.	MAN & GRAUE et, N.W. C 20036	R PLLC	3- v <b></b> -	··	

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#### PATENT APPLICATION

Attorney Docket No.: KWM-0001

Examiner: P. Greene

Confirmation No. 1108

Art Unit: 2826

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Kazutaka SHIBATA

Application No.: 10/088,163

Filed: March 15, 2002

SEMICONDUCTOR DEVICE WITH CHIP-ON-CHIP CONSTRUCTION JOINED

VIA A LOW-MELTING POINT METAL LAYER (As Amended)

AMENDMENT UNDER 37 C.F.R. §1.111

**BOX NON-FEE AMENDMENT** 

Commissioner for Patents Washington, DC 20231

Sir:

For:

In response to the Office Action dated December 18, 2002, please angend the above-identified application as follows:

### IN THE SPECIFICATION:

Please change the title of the invention as set forth below in clean form. Additionally, in accordance with 37 CFR 1.121(b)(1)(iii), the changed title is set forth in a marked-up version in the page(s) attached to this Amendment.

On Page 1, before Paragraph 1:

SEMICONDUCTOR DEVICE WITH CHIP-ON-CHIP CONSTRUCTION
JOINED VIA A LOW-MELTING POINT METAL LAYER

### IN THE CLAIMS:

Please cancel claims 21-24 without prejudice or disclaimer.

Please amend claims 1-6, 10, 12 and 18 as set forth below in clean form. Additionally, in accordance with 37 CFR 1.121(c)(1)(ii), the amended claim(s) are set forth in a marked-up version in the page(s) attached to this Amendment.

(Amended) A semiconductor device comprising:
 a first semiconductor chip having an electrode terminal:



3//8/03 INFD: \_\_\_\_